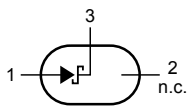


Schottky Diodes

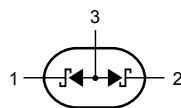
BAS70/A/C/S (KAS70/A/C/S)

■ Features

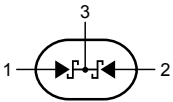
- Fast Switching Speed
- High breakdown voltage



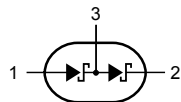
BAS70 single diode.



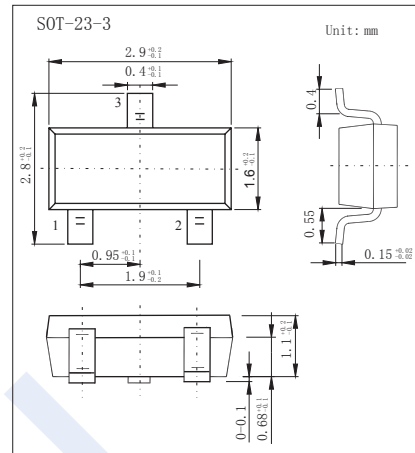
BAS70A



BAS70C



BAS70-S



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_{RM}	70	V
Peak Reverse Voltage	V_{RRM}	70	
Average Rectified Current at Temp=25°C	I_{FAV}	200	mA
Non-Repetitive Peak Forward Surge Current $t=1s$	I_{FSM}	600	
Power Dissipation	P_d	225	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 10 \mu\text{A}$	70			V
Forward voltage	V_{F1}	$I_F = 1 \text{ mA}$			0.41	
	V_{F2}	$I_F = 10 \text{ mA}$			0.75	
	V_{F3}	$I_F = 15 \text{ mA}$			1	
Reverse voltage leakage current	I_{R1}	$V_R = 70 \text{ V}$			1	μA
	I_{R2}	$V_R = 50 \text{ V}$			0.1	
Junction capacitance	C_j	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			2	pF

■ Marking

NO.	BAS70	BAS70A	BAS70C	BAS70S
Marking	A70	A72	A73	A74

Schottky Diodes

BAS70/A/C/S (KAS70/A/C/S)

■ Typical Characteristics

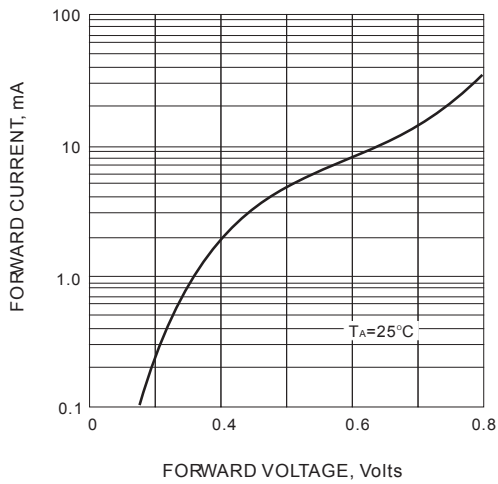


FIG. 1-TYPICAL FORWARD CHARACTERISTIC

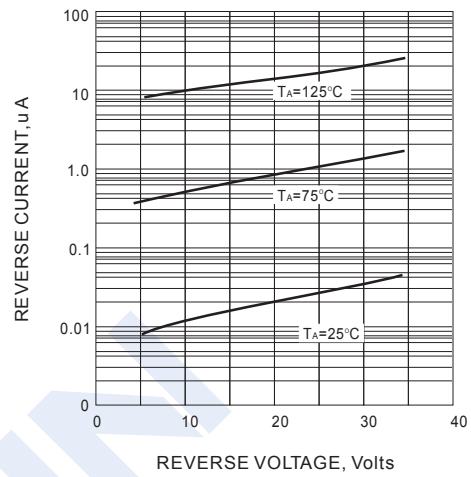


FIG. 2-TYPICAL REVERSE CHARACTERISTICS

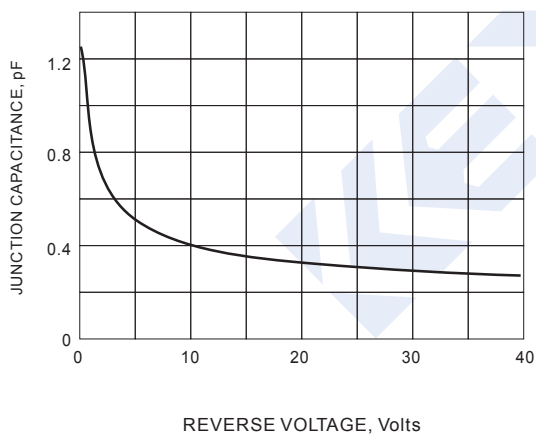


FIG. 3 TYPICAL JUNCTION CAPACITANCE

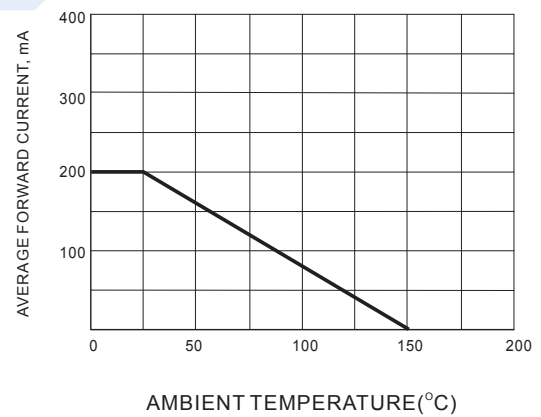


FIG. 4 FORWARD CURRENT DERATING